

**FIELD EFFECT TRANSISTORS WITH IMPROVED IMPLANTS AND METHOD
FOR MAKING SUCH TRANSISTORS**

ABSTRACT

Metal oxide semiconductor field effect transistor (MOSFET) (20) comprising a drain region (22) and source region (24) adjacent to a channel region (27). A gate oxide (28) is situated on the channel region (27) and a gate conductor (23) with vertical side walls (26) is placed on the gate oxide (28). The MOSFET (20) further comprises a threshold adjust implant region (71) and/or punch through implant region (71) being aligned with respect to the gate conductor (23) and limited to an area underneath the gate conductor (23).

Fig.2

This Sheet Has Been Replaced



THIS SHEET HAS BEEN
REPLACED